| | | | Max | Unit |
|---|---|---|---|---|
| | | | | |
| | | | - | V |
| | | | 1 | μA |
| | | | 100 | nA |
| | | | 100 | nA |
| | | | | |
| | | | | |
| | | | 4 | V |
| | | | | |
| | | | | |
| | | | - | S |
| | | | | pF |
| | | | | pF |
| | | | | pF |
| | | | | |
| | | | | ns |
| | | | | ns |
| | | | | ns |
| | | | | ns |
| | | | | nC |
| | | | | nC |
| | | | | nC |
| | | | | |
| | | | | A |

## TYPICAL CHARACTERISTICS

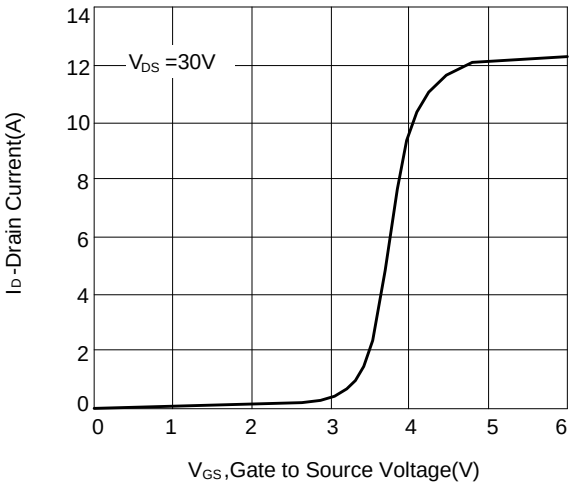


Figure 1: Transfer Characteristics

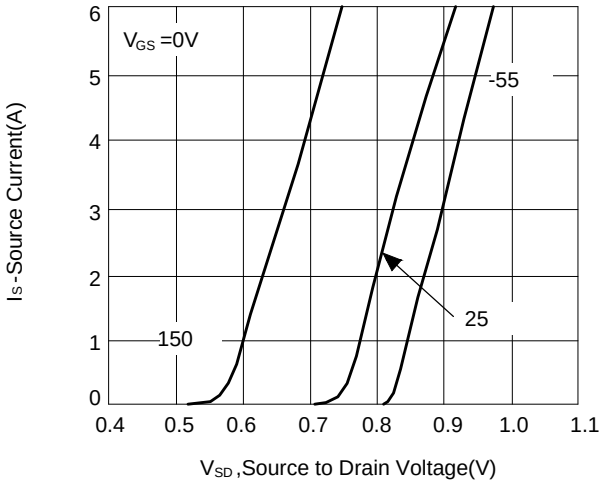


Figure 2: Body Diode Characteristics

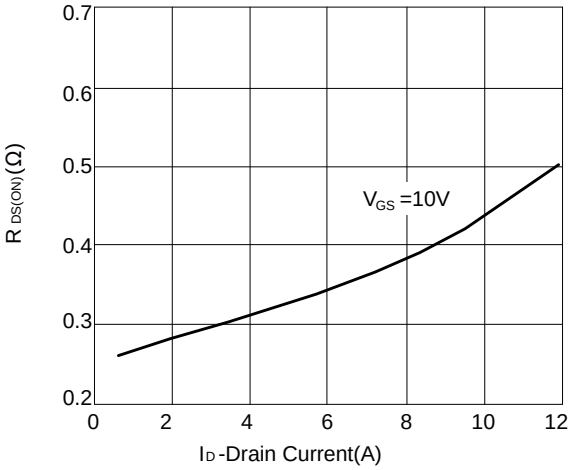


Figure 3: Drain to Source On-Resistance vs Drain Current

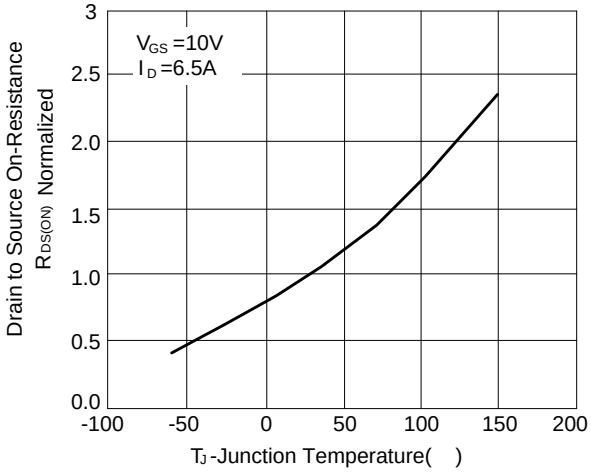


Figure 4: Drain to Source On-Resistance vs.Junction Temperature

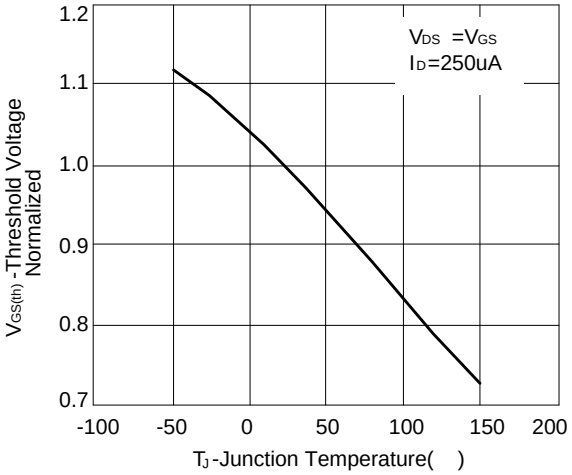


Figure 5: Threshold Voltage vs Junction Temperature

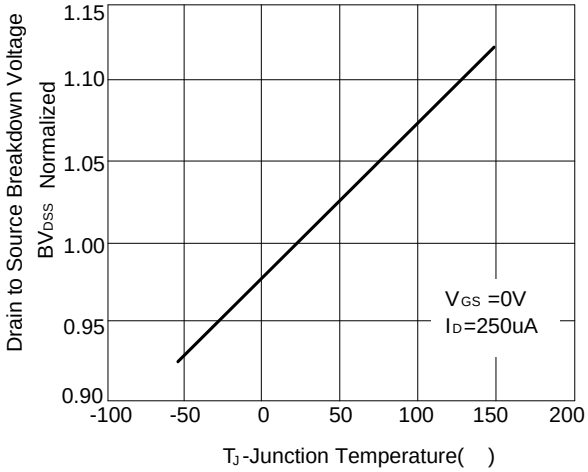


Figure 6: Breakdown Voltage vs Junction Temperature

TYPICAL CHARACTERISTICS(Cont.)

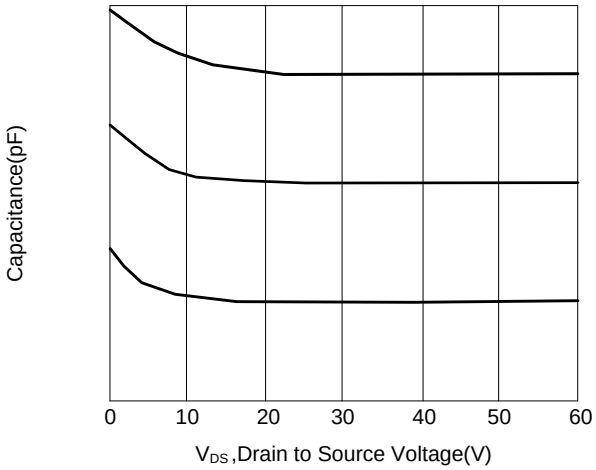


Figure 7: Capacitance vs Drain to Source Voltagfe

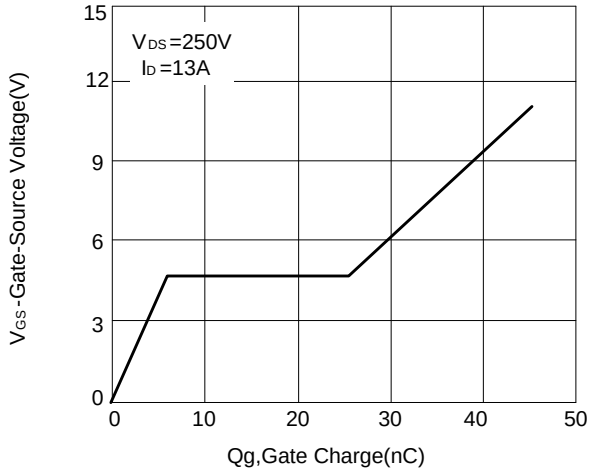


Figure 8: Gate Charge vs Gate to Source Voltage

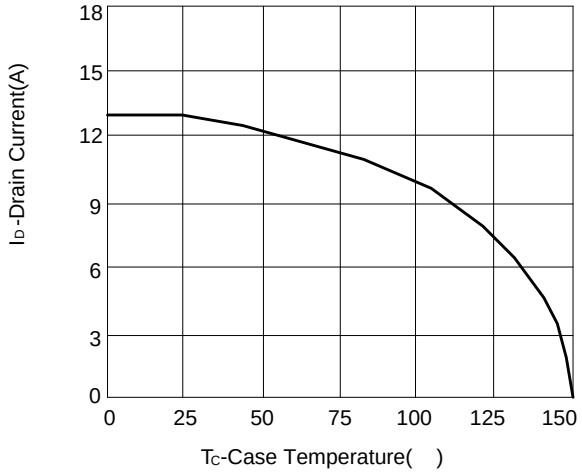


Figure 9: Continuous Drain vs Case Temperature

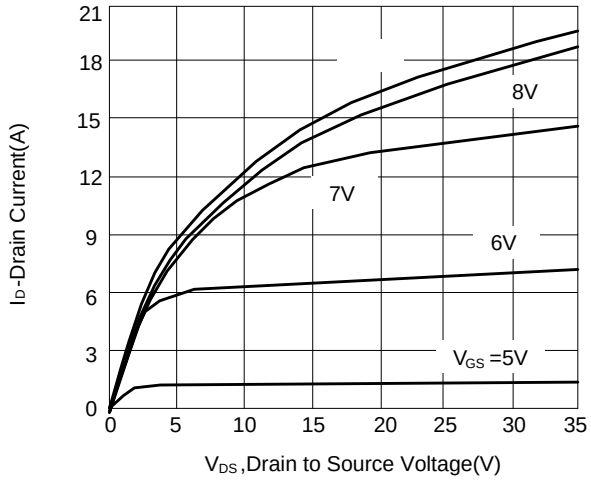


Figure 10: Output Characteristics

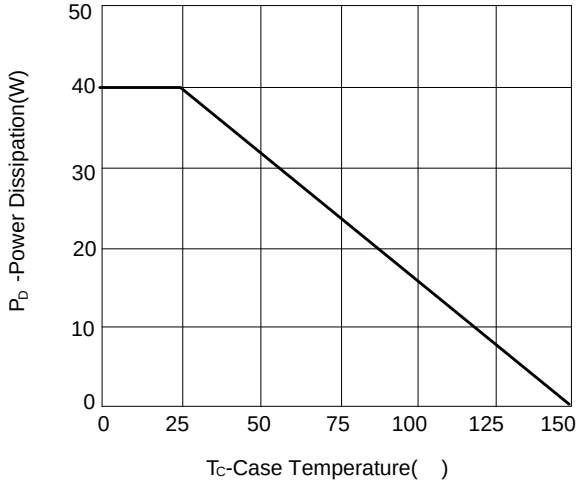


Figure 11: Power Dissipation vs Case Temperature

